

CD40106B Types

CMOS Hex Schmitt Triggers

High-Voltage Types (20-Volt Rating)

■ CD40106B consists of six Schmitt-trigger circuits. Each circuit functions as an inverter with Schmitt-trigger action on the input. The trigger switches at different points for positive- and negative-going signals. The difference between the positive-going voltage (V_P) and the negative-going voltage (V_N) is defined as hysteresis voltage (V_H) (see Fig.6).

The CD4013B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic package (E suffix), 14-lead small-outline package (NSR suffix), and in chip form (H suffix).

Features:

- Schmitt-trigger action with no external components
- Hysteresis voltage (typ.) 0.9 V at $V_{DD} = 5\text{ V}$, 2.3 V at $V_{DD} = 10\text{ V}$, and 3.5 V at $V_{DD} = 15\text{ V}$
- Noise immunity greater than 50%
- No limit on input rise and fall times
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of $1\ \mu\text{A}$ at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Low V_{DD} to V_{SS} current during slow input ramp
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators

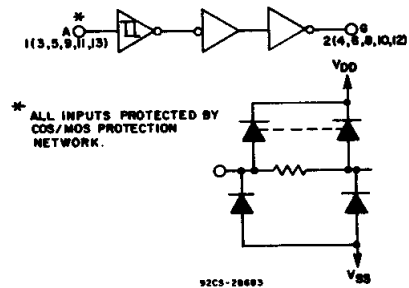
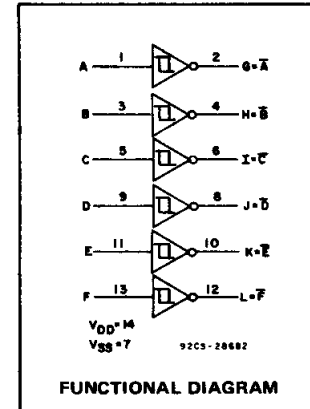


Fig.1 – Logic diagram (1 of 6 Schmitt triggers).

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})	-0.5V to +20V
Voltages referenced to V_{SS} Terminal)	
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to $V_{DD} + 0.5\text{ V}$
DC INPUT CURRENT, ANY ONE INPUT	$\pm 10\text{ mA}$
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$	500mW
For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$	Derate Linearity at 12mW/ $^\circ\text{C}$ to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$	100mW
OPERATING-TEMPERATURE RANGE (T_A)	-55°C to $+125^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})	-65°C to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79mm) from case for 10s max	$+265^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A Full Package-Temperature Range)	3	18	V

DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ\text{C}$, Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS	
		V_{DD} (V)	TYP.		MAX.
Propagation Delay Time:		5	140	280	ns
		10	70	140	
		15	60	120	
Transition Time:		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{iN}	Any Input		5	7.5	pF

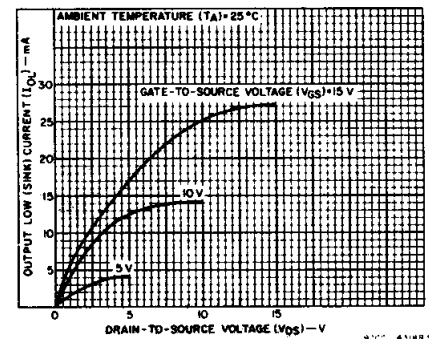


Fig.2 – Typical output low (sink) current characteristics.

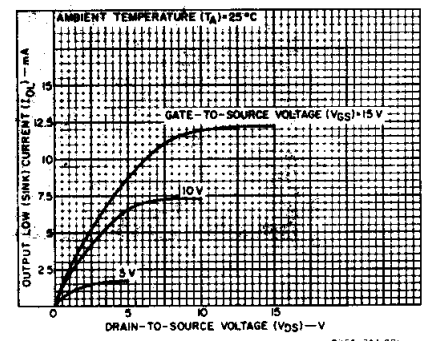
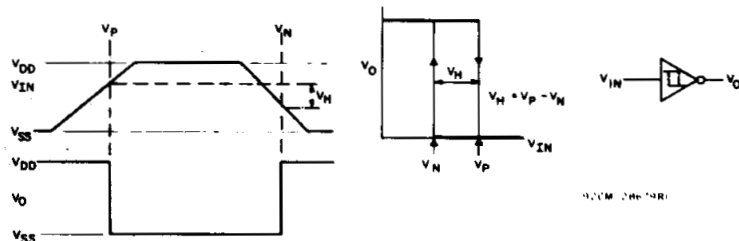


Fig.3 – Minimum output low (sink) current characteristics.

CD40106B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	-	0,5	5	1	1	30	30	-	0,02	1	μA
	-	0,10	10	2	2	60	60	-	0,02	2	
	-	0,15	15	4	4	120	120	-	0,02	4	
	-	0,20	20	20	20	600	600	-	0,04	20	
Positive Trigger Threshold Voltage V _P Min.	-	-	5	2,2	2,2	2,2	2,2	2,2	2,9	-	V
	-	-	10	4,6	4,6	4,6	4,6	4,6	5,9	-	
	-	-	15	6,8	6,8	6,8	6,8	6,8	8,8	-	
V _P Max.	-	-	5	3,6	3,6	3,6	3,6	-	2,9	3,6	V
	-	-	10	7,1	7,1	7,1	7,1	-	5,9	7,1	
	-	-	15	10,8	10,8	10,8	10,8	-	8,8	10,8	
Negative Trigger Threshold Voltage V _N Min.	-	-	5	0,9	0,9	0,9	0,9	0,9	1,9	-	V
	-	-	10	2,5	2,5	2,5	2,5	2,5	3,9	-	
	-	-	15	4	4	4	4	4	5,8	-	
V _N Max.	-	-	5	2,8	2,8	2,8	2,8	-	1,9	2,8	V
	-	-	10	5,2	5,2	5,2	5,2	-	3,9	5,2	
	-	-	15	7,4	7,4	7,4	7,4	-	5,8	7,4	
Hysteresis Voltage V _H Min.	-	-	5	0,3	0,3	0,3	0,3	0,3	0,9	-	V
	-	-	10	1,2	1,2	1,2	1,2	1,2	2,3	-	
	-	-	15	1,6	1,6	1,6	1,6	1,6	3,5	-	
V _H Max.	-	-	5	1,6	1,6	1,6	1,6	-	0,9	1,6	V
	-	-	10	3,4	3,4	3,4	3,4	-	2,3	3,4	
	-	-	15	5	5	5	5	-	3,5	5	
Output Low (Sink) Current, I _{OL} Min.	0,4	0,5	5	0,64	0,61	0,42	0,36	0,51	1	-	mA
	0,5	0,10	10	1,6	1,5	1,1	0,9	1,3	2,6	-	
	1,5	0,15	15	4,2	4	2,8	2,4	3,4	6,8	-	
Output High (Source) Current, I _{OH} Min.	4,6	0,5	5	-0,64	-0,61	-0,42	-0,36	-0,51	-1	-	mA
	2,5	0,5	5	-2	-1,8	-1,3	-1,15	-1,6	-3,2	-	
	9,5	0,10	10	-1,6	-1,5	-1,1	-0,9	-1,3	-2,6	-	
	13,5	0,15	15	-4,2	-4	-2,8	-2,4	-3,4	-6,8	-	
Output Voltage Low-Level, V _{OL} Max.	-	5	5	0,05				-	0	0,05	V
	-	10	10	0,05				-	0	0,05	
	-	15	15	0,05				-	0	0,05	
Output Voltage High Level, V _{OH} Min.	-	0	5	4,95				4,95	5	-	V
	-	0	10	9,95				9,95	10	-	
	-	0	15	14,95				14,95	15	-	
Input Current, I _{IN} Max.	-	0,18	18	±0,1	±0,1	±1	±1	-	±10 ⁻⁵	±0,1	μA



a) Definition of V_P, V_N, V_H
b) Transfer characteristics of 1 of 6 gates
Fig. 6 - Hysteresis definition, characteristics, and test set-up.

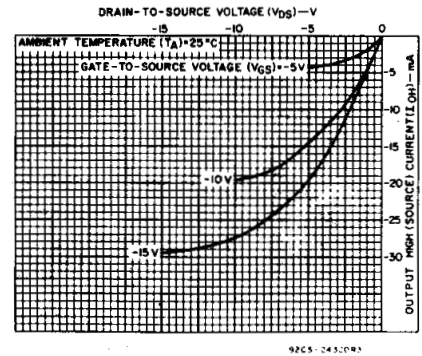


Fig. 4 - Typical output high (source) current characteristics.

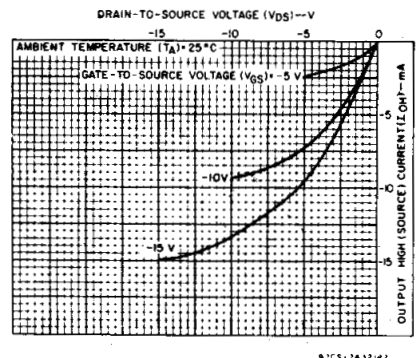


Fig. 5 - Minimum output high (source) current characteristics.

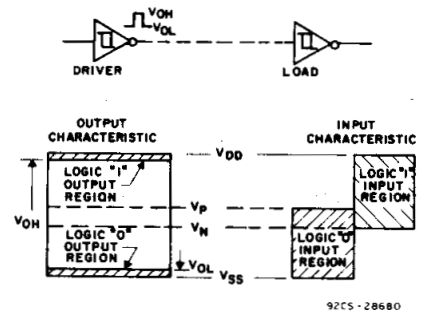


Fig. 7 - Input and output characteristics.

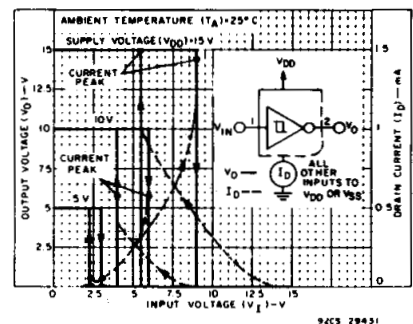


Fig. 8 - Typical current and voltage transfer characteristics.

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD40106B Types

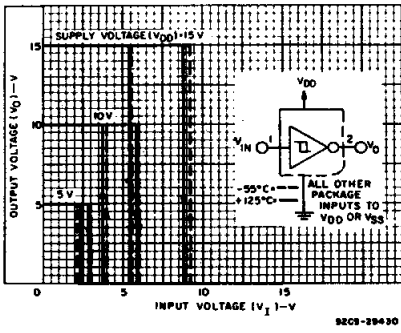


Fig. 9 - Typical voltage transfer characteristics as a function of temperature.

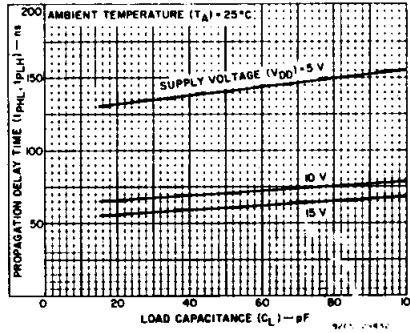


Fig. 10 - Typical propagation delay time as a function of load capacitance.

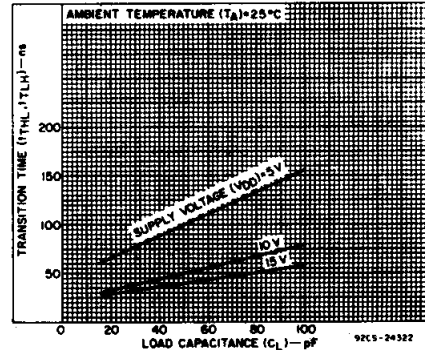


Fig. 11 - Typical transition time as a function of load capacitance.

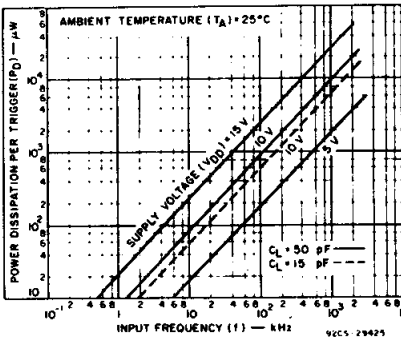


Fig. 12 - Typical power dissipation per trigger as a function of input frequency.

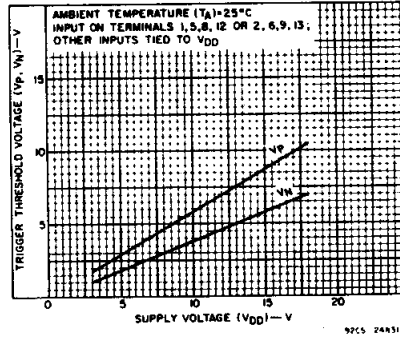


Fig. 13 - Typical trigger threshold voltage as a function of supply voltage.

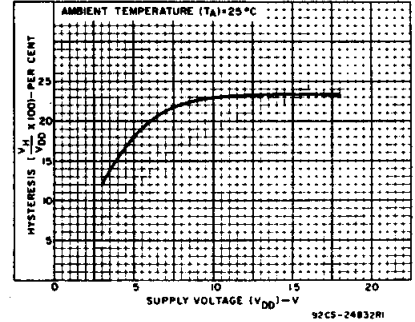


Fig. 14 - Typical per cent hysteresis as a function of supply voltage.

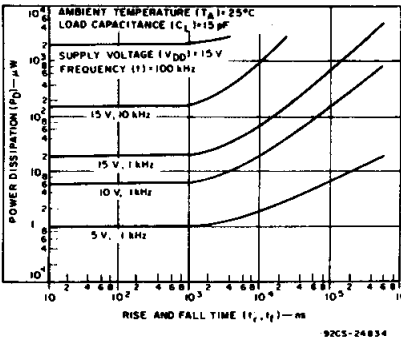


Fig. 15 - Typical power dissipation as a function of rise and fall times.

APPLICATIONS

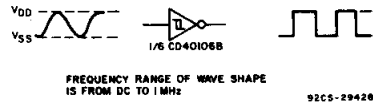


Fig. 16 - Wave shaper.

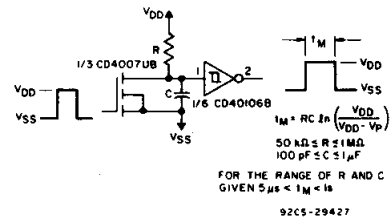


Fig. 17 - Monostable multivibrator.

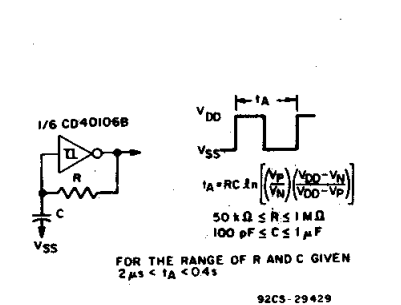


Fig. 18 - Astable multivibrator.

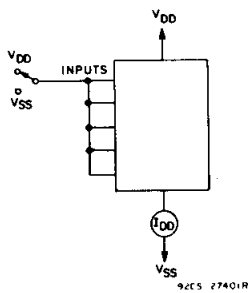


Fig. 19 - Quiescent device current test circuit.

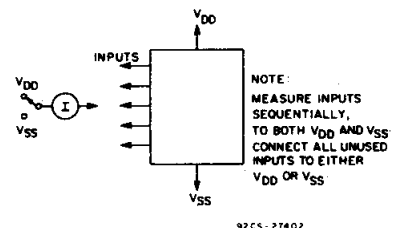


Fig. 20 - Input current test circuit.

CD40106B Types

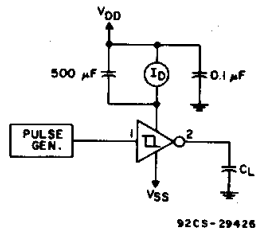
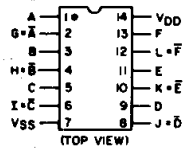
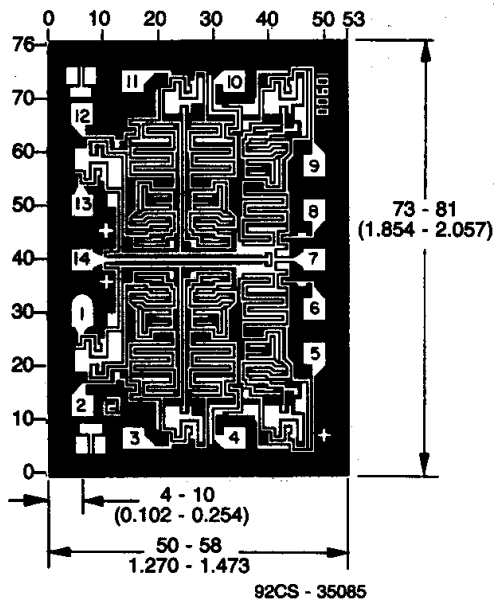


Fig.21 – Dynamic power dissipation test circuit.



TERMINAL ASSIGNMENT



Dimensions and Pad Layout for CD40106BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Mailing Address:

Texas Instruments
Post Office Box 655303
Dallas, Texas 75265